Thank you for your interest in **onsemi** products.

Your technical document begins on the following pages.

Your Feedback is Important to Us!

Please take a moment to participate in our short survey.
At **onsemi**, we are dedicated to delivering technical content that best meets your needs.

Help Us Improve – Take the Survey

This survey is intended to collect your feedback, capture any issues you may encounter, and to provide improvements you would like to suggest.

We look forward to your feedback.

To learn more about **onsemi**, please visit our website at
www.onsemi.com

Low Voltage Hex Buffer with Open Drain Outputs

74LCX07

General Description

The LCX07 contains six buffers. The inputs tolerate voltages up to 5.5 V allowing the interface of 5 V systems to 3 V systems.

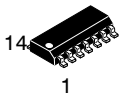
The outputs of the LCX07 are open drain and can be connected to other open drain outputsto implement active HIGH wire AND or active LOW wire OR functions.

The 74LCX07 is fabricated with advanced CMOS technology to achieve high speed operation while maintaining CMOS low power dissipation.

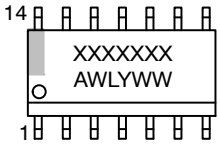
Features

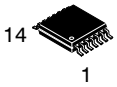
- 5 V Tolerant Inputs
- 1.65 V – 5.5 V V_{CC} Specifications Provided
- 2.9 ns t_{PD} Max. (V_{CC} = 3.3 V), 10 μA I_{CC} Max.
- Power Down High Impedance Inputs and Outputs
- ±24 mA Output Drive (V_{CC} = 3.0 V)
- Implements Proprietary Noise/EMI Reduction Circuitry
- Latch−up Performance Exceeds JEDEC 78 Conditions
- ESD performance:
  - Human Body Model >2000 V
- Available on SOIC, TSSOP and Leadless QFN Packages
- These Devices are Pb−Free, Halide Free and are RoHS Compliant

MARKING DIAGRAMS

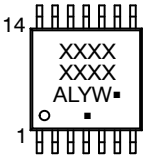


SOIC−14
D SUFFIX
CASE 751A



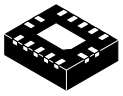


TSSOP−14
DT SUFFIX
CASE 948G



XXXXXX	= Specific Device Code
A	= Assembly Location
L, WL	= Wafer Lot
Y, YY	= Year
W, WW	= Work Week
G or ▪	= Pb−Free Package

(Note: Microdot may be in either location)



QFN14 3.0x2.5, 0.5P
CASE 510CB

XXXXX	= Specific Device Code
Z	= Assembly Plant Code
XY	= Date Code
KK	= Lot Run Traceability Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet.

CONNECTION DIAGRAMS

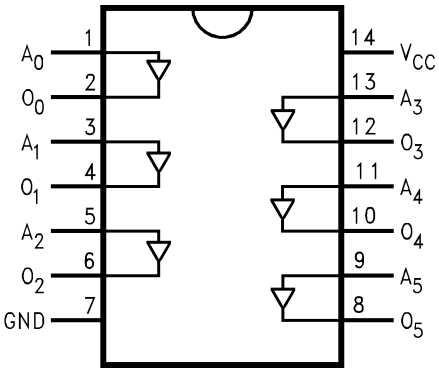


Figure 1. Pin Assignments for SOIC and TSSOP

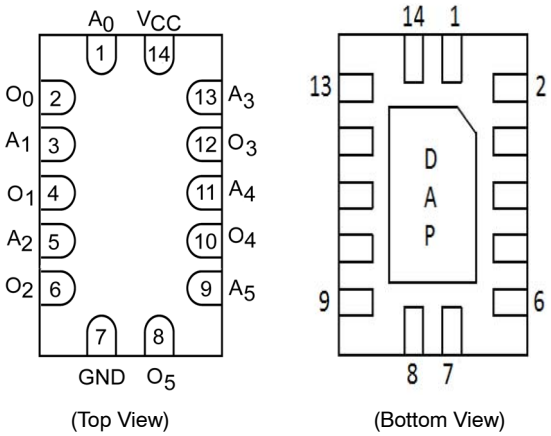


Figure 2. Pad Assignments for DQFN

LOGIC SYMBOL

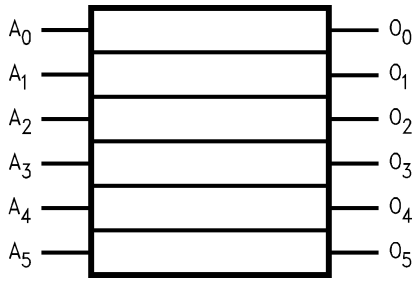


Figure 3. IEEE/IEC

PIN DESCRIPTION

Pin Names	Description
A_n	Inputs
O_n	Outputs
DAP	No Connect

NOTE: DAP (Die Attach Pad)

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to +6.5	V
V_I	DC Input Voltage (Note 1)		−0.5 to +6.5	V
V_O	DC Output Voltage (Note 1)	Active−Mode (High or Low State) Tri−State Mode Power−Down Mode (V_{CC} = 0 V)	−0.5 to V_{CC} + 0.5 −0.5 to +6.5 −0.5 to +6.5	V
I_{IK}	DC Input Diode Current	V_I < GND	−50	mA
I_{OK}	DC Output Diode Current	V_O < GND	−50	mA
I_O	DC Output Source/Sink Current		±50	mA
I_{CC} or I_{GND}	DC Supply Current per Supply Pin or Ground Pin		±100	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 secs		260	°C
T_J	Junction Temperature Under Bias		+150	°C
θ_{JA}	Thermal Resistance (Note 1)	SOIC−14 QFN14 TSSOP−14	116 130 150	°C/W
P_D	Power Dissipation in Still Air at 125°C	SOIC−14 QFN14 TSSOP−14	1077 962 833	mW
MSL	Moisture Sensitivity		Level 1	−
F_R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V−0 @ 0.125 in	−
V_{ESD}	ESD Withstand Voltage (Note 3)	Human Body Model Charged Device Model	2000 N/A	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. I_O absolute maximum rating must be observed.
2. Measured with minimum pad spacing on an FR4 board, using 76 mm−by−114 mm, 2−ounce copper trace no air flow per JESD51−7.
3. HBM tested to EIA / JESD22−A114−A. CDM tested to JESD22−C101−A. JEDEC recommends that ESD qualification to EIA/JESD22−A115A (Machine Model) be discontinued.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Typ	Max	Unit
V_{CC}	Supply Voltage	Operating Data Retention Only	1.65 1.5	3.3 3.3	5.5 5.5	V
V_I	Digital Input Voltage		0	−	5.5	V
V_O	Output Voltage	Active Mode (High or Low State) Tri−State Mode Power Down Mode (V_{CC} = 0 V)	0 0 0	− − −	V_{CC} 5.5 5.5	V
T_A	Operating Free−Air Temperature		−40	−	+125	°C
t_r, t_f	Input Rise or Fall Rate	V_{CC} = 1.65 V to 1.95 V V_{CC} = 2.3 V to 2.7 V V_{IN} from 0.8 V to 2.0 V, V_{CC} = 3.0 V V_{CC} = 4.5 V to 5.5 V	0 0 0 0	− − − −	20 20 10 5	nS/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

4. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Conditions	V_{CC} (V)	T_A = −40°C to +85°C		T_A = −40°C to +125°C		Unit
				Min	Max	Min	Max	
V_{IH}	HIGH Level Input Voltage		1.65 – 1.95	0.65 x V_{CC}	–	0.65 x V_{CC}	–	V
			2.3 – 2.7	1.7	–	1.7	–	
			3.0 – 3.6	2.0	–	2.0	–	
			4.5 – 5.5	0.70 x V_{CC}	–	0.70 x V_{CC}	–	
V_{IL}	LOW Level Input Voltage		1.65 – 1.95	–	0.35 x V_{CC}	–	0.35 x V_{CC}	V
			2.3 – 2.7	–	0.7	–	0.7	
			3.0 – 3.6	–	0.8	–	0.8	
			4.5 – 5.5	–	0.30 x V_{CC}	–	0.30 x V_{CC}	
V_{OL}	Low−Level Output Voltage	V_I = V_{IH} or V_{IL}						V
		I_{OL} = 100 μA	1.65 – 5.5	–	0.1	–	0.1	
		I_{OL} = 4 mA	1.65	–	0.24	–	0.24	
		I_{OL} = 8 mA	2.3	–	0.3	–	0.3	
		I_{OL} = 12 mA	2.7	–	0.4	–	0.4	
		I_{OL} = 16 mA	3.0	–	0.4	–	0.4	
		I_{OL} = 24 mA	3.0	–	0.55	–	0.55	
		I_{OL} = 32 mA	4.5	–	0.6	–	0.6	
I_I	Input Leakage Current	V_I = 0 to 5.5 V	1.65 – 5.5	–	±5.0	–	±5.0	μA
I_{OZ}	Off−State Leakage Current	V_O = 5.5 V	1.65 – 5.5	–	10	–	10	μA
I_{OFF}	Power Off Leakage Current	V_I = 5.5 V or V_O = 5.5 V	0	–	10	–	10	μA
I_{CC}	Quiescent Supply Current	V_I = 5.5 V or GND	5.5	–	10	–	10	μA
ΔI_{CC}	Increase in I_{CC} per Input	V_{IH} = V_{CC} – 0.6 V	2.3 – 3.6	–	500	–	500	μA
			4.5 – 5.5	–	1	–	1	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Condition	V_{CC} (V)	T_A = −40°C to +85°C		T_A = −40°C to +125°C		Unit
				Min	Max	Min	Max	
t_{PZL}, t_{PLZ}	Propagation Delay, Input to Output	See Figures 4 and 5	1.65 –1.95	–	6.5	–	6.5	ns
			2.3 – 2.7	–	3.8	–	3.8	
			2.7	–	3.7	–	3.7	
			3.0 – 3.6	–	3.0	–	3.3	
			4.5 – 5.5	–	2.7	–	2.7	
t_{OSHL}, t_{OSLH}	Output to Output Skew		1.65 – 1.95	–	–	–	–	ns
			2.3 – 2.7	–	–	–	–	
			2.7	–	–	–	–	
			3.0 – 3.6	–	1.0	–	1.0	
			4.5 – 5.5	–	–	–	–	

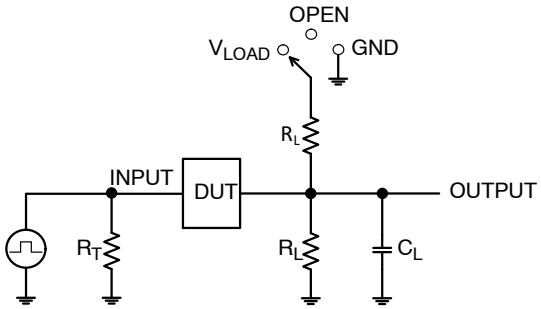
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

DYNAMIC SWITCHING CHARACTERISTICS

Symbol	Parameter	V_{CC} (V)	Conditions	T_A = 25°C	Unit
				Typical	
V_{OLP}	Quiet Output Dynamic Peak V_{OL}	3.3	C_L = 50 pF, V_{IH} = 3.3 V, V_{IL} = 0 V	0.9	V
		2.5	C_L = 30 pF, V_{IH} = 2.5 V, V_{IL} = 0 V	0.7	
V_{OLV}	Quiet Output Dynamic Valley V_{OL}	3.3	C_L = 50 pF, V_{IH} = 3.3 V, V_{IL} = 0 V	–0.8	V
		2.5	C_L = 30 pF, V_{IH} = 2.5 V, V_{IL} = 0 V	–0.6	

CAPACITANCE

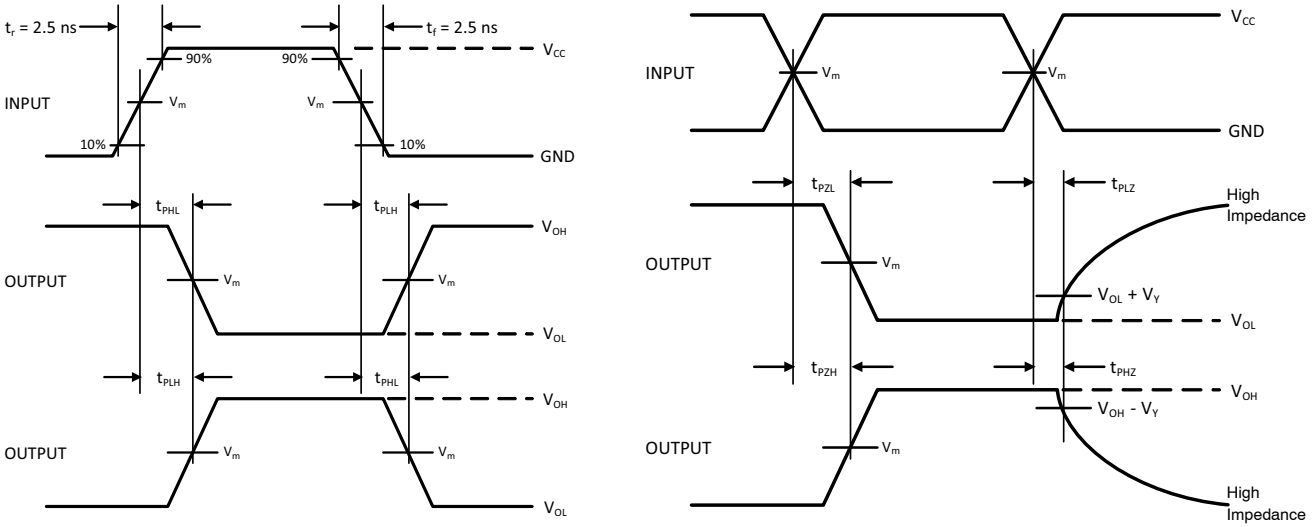
Symbol	Parameter	Conditions	Typical	Unit
C_{IN}	Input Capacitance	V_{CC} = Open, V_I = 0 V or V_{CC}	7	pF
C_{OUT}	Output Capacitance	V_{CC} = 3.3 V, V_I = 0 V or V_{CC}	8	pF
C_{PD}	Power Dissipation Capacitance	V_{CC} = 3.3 V, V_I = 0 V or V_{CC}, f = 10 MHz	25	pF



Test	Switch Position
t_{PLH} / t_{PHL}	Open
t_{PLZ} / t_{PZL}	V_{LOAD}
t_{PHZ} / t_{PZH}	GND

C_L includes probe and jig capacitance
R_T is Z_{OUT} of pulse generator (typically 50 Ω)
f = 1 Mhz, t_W = 500 ns

Figure 4. Test Circuit



V_{CC}, V	R_L, Ω	C_L, pF	V_{LOAD}	V_m, V	V_Y, V
1.65 to 1.95	500	30	2 x V_{CC}	V_{CC}/2	0.15
2.3 to 2.7	500	30	2 x V_{CC}	V_{CC}/2	0.15
2.7	500	50	6 V	1.5	0.3
3.0 to 3.6	500	50	6 V	1.5	0.3
4.5 to 5.5	500	50	2 x V_{CC}	V_{CC}/2	0.3

Figure 5. Switching Waveforms

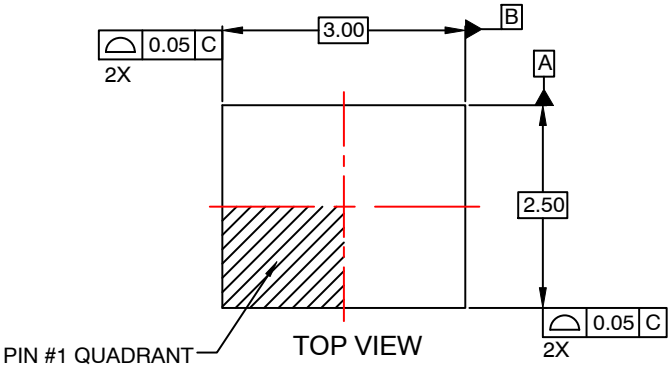
ORDERING INFORMATION

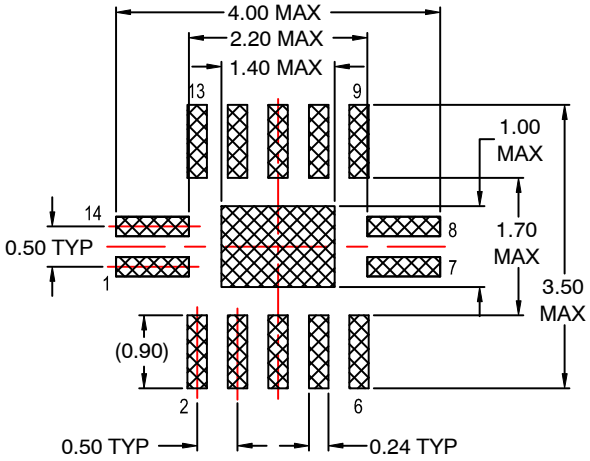
Device	Marking	Package	Shipping†
74LCX07MTCX	LCX 07	TSSOP−14	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

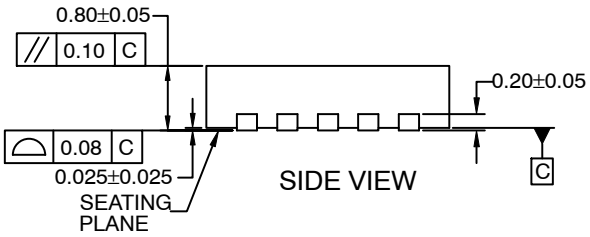
QFN14 3.0x2.5, 0.5P
CASE 510CB
ISSUE O

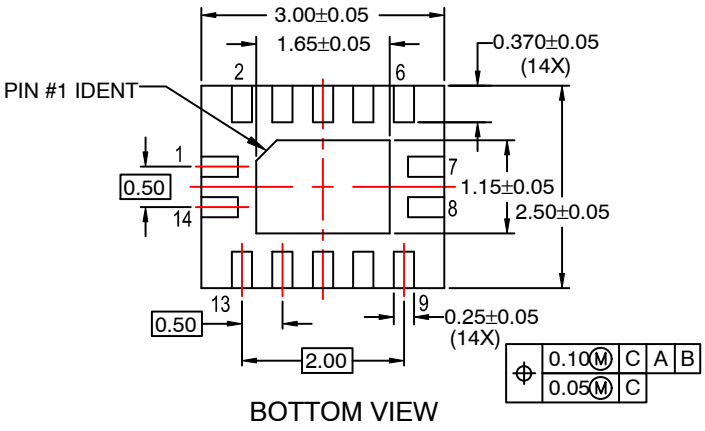
DATE 31 AUG 2016





RECOMMENDED LAND PATTERN





NOTES:

A. CONFORMS TO JEDEC REGISTRATION MO−241, VARIATION AA

B. DIMENSIONS ARE IN MILLIMETERS.

C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.

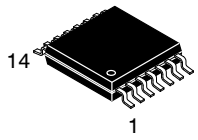
D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.

DOCUMENT NUMBER:	**98AON13643G**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	**QFN14 3.0X2.5, 0.5P**	**PAGE 1 OF 1**

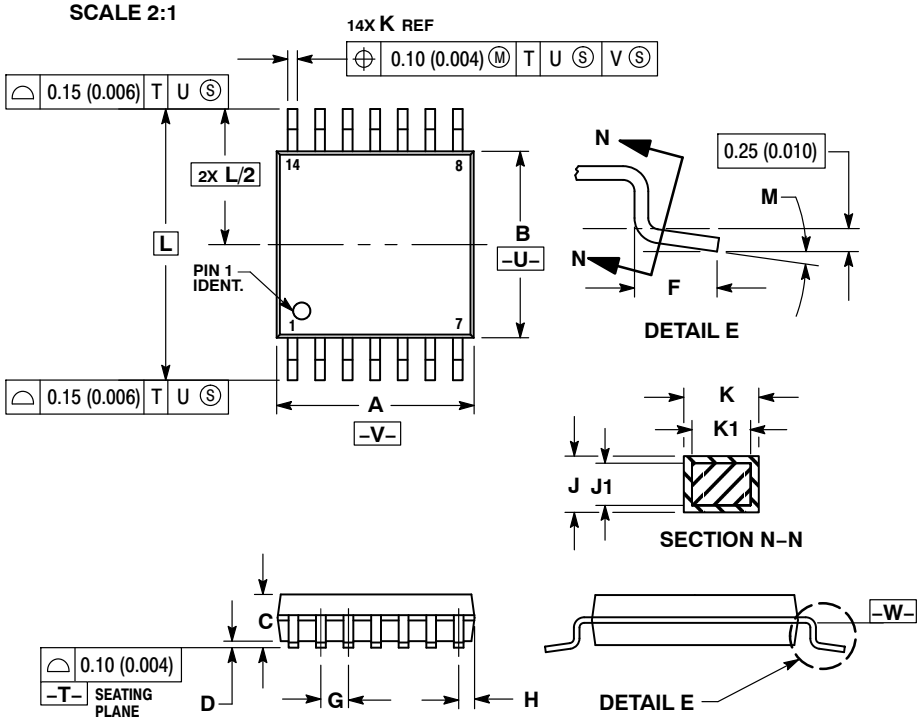
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

TSSOP−14 WB
CASE 948G
ISSUE C

DATE 17 FEB 2016



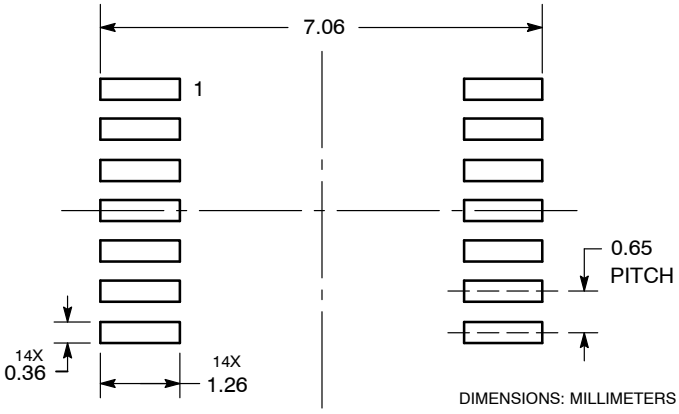
SCALE 2:1



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

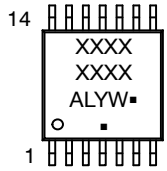
	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	−−−	1.20	−−−	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0 °	8 °	0 °	8 °

SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	**98ASH70246A**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	**TSSOP−14 WB**	**PAGE 1 OF 1**

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales